



NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF890** is Designed for UHF Class A Amplifier Applications in Cellular Base Station Equipment.

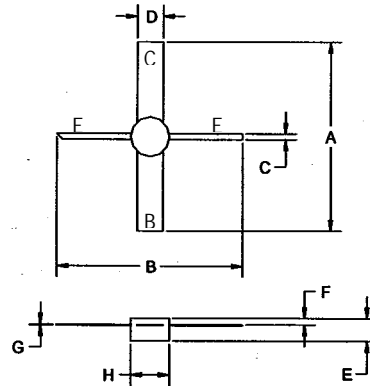
FEATURES:

- $P_g = 9.0$ dB min. @ 900 MHz
- $P_{1dB} = 2.0$ Watts min. at 900 MHz
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	0.5 A
V_{CBO}	55 V
V_{CER}	30 V
V_{EBO}	4.0 V
P_{DISS}	7.0 W @ $T_C = 25^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+150^\circ\text{C}$
θ_{JC}	25°C/W

PACKAGE STYLE .205 4L STUD



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.976 / 24.800	1.00 / 25.400
B	.976 / 24.800	1.00 / 25.400
C	.028 / 0.700	.031 / 0.800
D	.138 / 3.500	
E	.106 / 2.700	.139 / 3.400
F	.039 / 1.000	.047 / 1.200
G	.004 / 0.100	.006 / 0.150
H	.200 / 5.100	.208 / 5.300

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	$I_C = 5.0$ mA	30			V
BV_{CES}	$I_C = 5.0$ mA	55			V
BV_{EBO}	$I_E = 5.0$ mA	4.0			V
I_{CBO}	$V_{CB} = 30$ V			500	μA
h_{FE}	$V_{CE} = 5.0$ V $I_C = 100$ mA	10		100	---
C_{OB}	$V_{CB} = 30$ V $f = 1.0$ MHz			2.0	pF
P_G	$V_{CC} = 24$ V $P_{OUT} = 2.0$ V $f = 900$ MHz	9.0			dB
η_C		55			%

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Specifications are subject to change without notice.